

Tool ID: 117  
Tool Location: 103

## Equipment Information Sheet CMOS Gate Oxide - E1

**Manager:** Phil Infante  
**Backup:** Aaron Windsor

607-254-4926  
607-254-4831

Calls to staff phones will be automatically forwarded to their cell phones during accessible hours. At other times leave a message or send them an email.

### SAFETY

- The furnaces are run at elevated temperatures of 400-1200°C and use flammable, toxic, and corrosive gases.

### USAGE RESTRICTIONS

- No changing of gas flows or process parameters without staff approval
- Max process temperature of 1100 C

### SCHEDULING/SIGN-UP RESTRICTIONS

- Reservation blocks greater than 8 hrs must be cleared by a MOS staff person prior to reserving the time

*Minimum Tool Time: 90 minutes*

### MATERIALS COMPATIBILITY CATEGORY

#### Tool Category 1: Restrictd Silicon Based Materials Only

Allowed	Not Allowed
Silicon Based Materials only (Si, SiC, SiO <sub>2</sub> substrates)	No Evaporated, Sputtered, or Spin on Films
All Furnace grown or deposited films	No ALD films
PECVD Films	No Metal or Organic Films
	No Glass Substrates
	No III/V Compound Semiconductors
	No Deep Silicon Etched Samples (versaline, Unaxis)
	No Organic/Biology Molecules prepared-with or without Salt buffers

### Additional Material Restrictions and Exceptions

- MOS CLEAN required prior to use
- Only use MOS designated holders and wands

*Last Updated: 03/20/2019*